

# ZERO BIAS SCHOTTKY DIODE

#### **DESCRIPTION:**

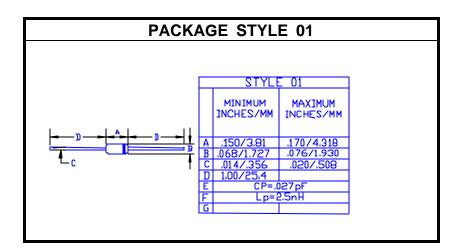
The **HSCH-3486** is a Silicon Zero Bias Schottky Barrier Diode Designed for High Sensitivity Detector and Low Starved Mixer Applications up to 10 GHz.

## FEATURES INCXLUDE:

- Replacement for HSCH3486 and MA4E928B-54
- True Zero Bias Operation
- Hermetic Glass Package

#### **MAXIMUM RATINGS**

IF	10 mA				
V <sub>R</sub>	2.0 V				
P <sub>DISS</sub>	$300 \text{ mW} @ \text{T}_{\text{C}} = 25 \ ^{\text{O}}\text{C}$				
ТJ	-65 <sup>o</sup> C to +150 <sup>o</sup> C				
T <sub>STG</sub>	-65 <sup>o</sup> C to +150 <sup>o</sup> C				
$\mathbf{T}_{SOLD}$	+230 <sup>O</sup> C for 5 seconds				



## **CHARACTERISTICS** $T_c = 25 °C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V <sub>F</sub>	l <sub>F</sub> = 1.0 mA				225	mV
C <sub>T</sub>	V <sub>R</sub> = 0 V	f = 1.0 MHz			0.5	pF
T <sub>ss</sub>	B <sub>W</sub> = 2.0 MHz	f = 10 GHz			-54	dBm
g	P <sub>IN</sub> = -40 dBm	f = 10 GHz	7.5			mV/ <b>mi</b> W
Rv	P <sub>IN</sub> = -40 dBm	f = 10 GHz	2		8	K ohms

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